

An IATF 16949, ISO9001 and ISO 14001 Certified Company

Switchmode Serier NPN Silicon Power Transistor

15 AMPERES, 300 and 400 VOLTS, 175 WATTS



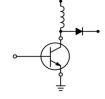


2N6546 2N6547

TO-3 Metal Can Package

RoHS compliant





FEATURES:

The 2N6547 transistor is designed for high–voltage, high–speed, power switching in inductive circuits where fall time is critical. They are particularly suited for 115 and 220 volt line operated switch–mode applications Specification Features —

High Temperature Performance Specified for:

Reversed Biased SOA with Inductive Loads

Switching Times with Inductive Loads

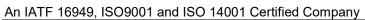
Saturation Voltages

Leakage Currents

APPLICATIONS:

- 1. Switching Regulators
- 2. PWM Inverters and Motor Controls
- 3. Solenoid and Relay Drivers
- 4. Deflection Circuits









ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO(sus)	400	Vdc
Collector–Emitter Voltage	VCEX(sus)	450	Vdc
Collector–Emitter Voltage	VCEV	850	Vdc
Emitter Base Voltage	VEB	9.0	Vdc
Collector Current — Continuous — Peak (2)	I _C	15 30	Adc
Base Current — Continuous — Peak (2)	I _B	10 20	Adc
Emitter Current — Continuous — Peak (2)	I _E	25 35	Adc
Total Power Dissipation @ T _C = 25°C @ T _C = 100°C Derate above 25°C	PD	175 100 1.0	Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R JC	1.0	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8 from Case for 5 Seconds	T∟	275	°C









ELECTRICAL CHARACTERISTICS (T_A=25 ° C unless otherwise specified)

	Characteristic	8	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (1)		<u> </u>		9	9
Collector-Emitter Sustainin (IC = 100 mA, IB = 0)	2N6546 2N6547	VCEO(sus)	300 400	=	Vdc	
Collector-Emitter Sustainir	ng Voltage		VCEX(sus)			Vdc
	ated V _{CEX} , T _C = 100°C)	2N6546	OLA(SUS)	350		
		2N6547		450	_	1
(I _C = 15 A, V _{clamp} = Ra T _C = 100°C)	ted VCEO = 100 V,	2N6546 2N6547		200 300	=	
Collector Cutoff Current			ICEV			mAdd
(V _{CEV} = Rated Value, V			0.000,000,000	_	1.0	100,000,000
(VCEV = Rated Value, V	BE(off) = 1.5 Vdc, T _C = 100°C)			_	4.0	1
Collector Cutoff Current (VCE = Rated VCEV, Re	s= = 50 . T _C = 100°C)		^I CER	-	5.0	mAdd
Emitter Cutoff Current	2		I _{EBO}	_	1.0	mAde
(VEB = 9.0 Vdc, IC = 0)			-280			
SECOND BREAKDOWN						
	tor Current with base forward biased		Is/b	0.2	-	Adc
t = 1.0 s (non-repetitive)	(VCE = 100 Vdc)					
ON CHARACTERISTICS (1)					
DC Current Gain	244.3		pEE	9,000	700000	_
(IC = 5.0 Adc, VCE = 2.0 (IC = 10 Adc, VCE = 2.0				1.2 6.0	60	1
(IC - 10 Mds, TCE - 2.0	7407			6.0	30	_
Collector-Emitter Saturation			VCE(sat)			Vdc
(IC = 10 Adc, IB = 2.0 Ad (IC = 15 Adc, IB = 3.0 Ad				_	1.5	1
(IC = 10 Adc, IB = 2.0 Ad				_	5.0 2.5	1
Base-Emitter Saturation V	oltage		V _{BE(sat)}			Vdc
(IC = 10 Adc, Ig = 2.0 Ad			· DE(Sat)	_	1.6	1.00
(IC = 10 Adc, IB = 2.0 Ad	dc, T _C = 100°C			-	1.6	
OYNAMIC CHARACTERIST	rics					
Current-Gain — Bandwidt			fτ	6.0	28	MHz
(IC = 500 mAdc, VCE =	10 Vdc, f _{test} = 1.0 MHz)		=3			
Output Capacitance (VCB = 10 Vdc, IE = 0, fe		C _{ob}	125	500	pF	
WITCHING CHARACTERI	STICS					
Resistive Load						
Delay Time			t _d	-	0.05	s
Rise Time	(V _{CC} = 250 V, I _C = 10 A,		tr	_	1.0	s
Storage Time	$I_{B1} = I_{B2} = 2.0 \text{ A}, I_p = 100 \text{ s},$ Duty Cycle $\leq 2.0\%$)	ts	722	4.0	s	
Fall Time	1	tf	_	0.7	s	
Inductive Load, Clamped						
Storage Time	(IC = 10 A(pk), V _{clamp} = Rated V _{CEX} , I _{B1} =	2.0 A,	ts	-	5.0	s
Fall Time				-	1.5	s
				Typ	ical	
Storage Time	(I _C = 10 A(pk), V _{clamp} = Rated V _{CEX} , I _{B1} =	2.0 A.	ts		.0	s

⁽¹⁾ Pulse Test: Pulse Width = 300 s, Duty Cycle = 2%.

2N6547

Rev0_30042020EM









TYPICAL CHARACTERISTICS CURVES

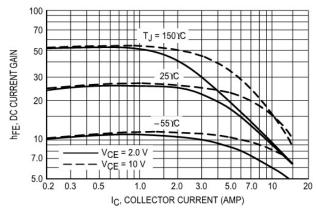


Figure 1. DC Current Gain

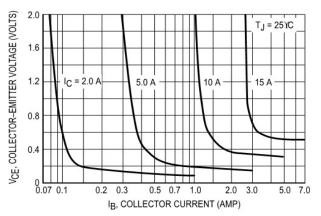


Figure 2. Collector Saturation Region

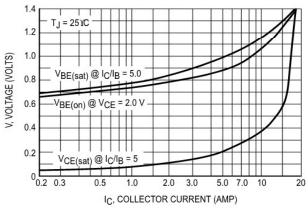


Figure 3. "On" Voltages

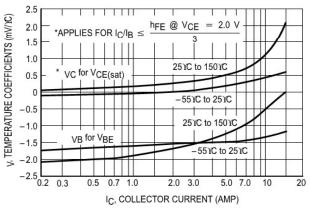


Figure 4. Temperature Coefficients

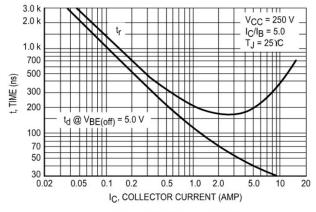


Figure 5. Turn-On Time

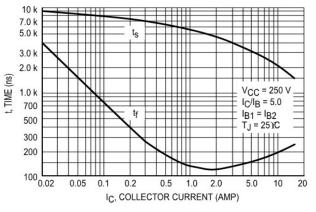
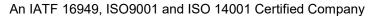


Figure 6. Turn-Off Time









TYPICAL CHARACTERISTICS CURVES

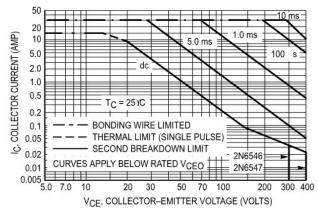


Figure 7. Forward Bias Safe Operating Area

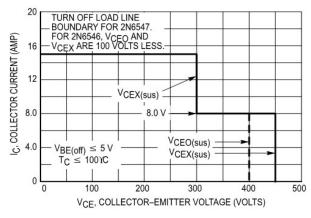


Figure 8. Reverse Bias Safe Operating Area

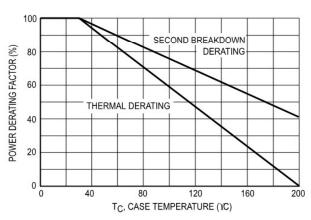


Figure 9. Power Derating

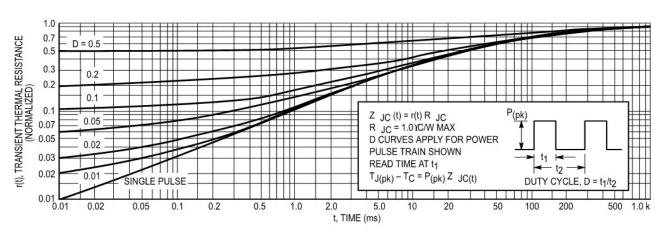


Figure 10. Thermal Response

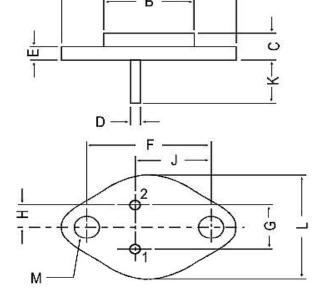






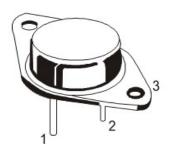


Package Details



All dimensions in mm.

DIM	MIN.	MAX.
Α	_	39.37
В	_	22.22
С	6.35	8.50
D	0.96	1.09
Е	_	1.77
F	29.90	30.40
G	10.69	11.18
Н	5.20	5.72
J	16.64	17.15
K	11.15	12.25
L		26.67
М	3.84	4.19



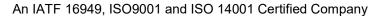
PIN CONFIGURATION

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
9	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-3	100 pcs/pkt	1.3 kg/100 pcs	12.5" x 8" x 1.8"	0.1K	17" x 11.5" x 21"	2K	27.5 kgs









Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level					
Level	Time	Condition			
1	Unlimited	≤30 °C / 85% RH			
2	1 Year	≤30 °C / 60% RH			
2a	4 Weeks	≤30 °C / 60% RH			
3	168 Hours	≤30 °C / 60% RH			
4	72 Hours	≤30 °C / 60% RH			
5	48 Hours	≤30 °C / 60% RH			
5a	24 Hours	≤30 °C / 60% RH			
6	Time on Label(TOL)	≤30 °C / 60% RH			







Customer Notes

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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